

AMENDMENTS TO THE CLAIMS

Claim 1 (currently amended): A bipolar junction transistor (BJT) comprising:

- 5 a substrate;
a dielectric layer formed on a predetermined region of the substrate;
an oxide layer and a silicon nitride layer stacked on the dielectric layer;
10 an opening formed in the dielectric layer, the oxide layer, and the silicon nitride layer, and a portion of the substrate being exposed;
a heavily doped polysilicon layer formed on a sidewall of the opening and on the substrate to
15 define a self-aligned base region in the opening;
an intrinsic base doped region formed within the substrate and in a bottom of the opening by implanting through the self-aligned base region;
a spacer formed on the heavily doped polysilicon layer to define a self-aligned emitter region
20 in the opening; and
an emitter conductivity layer being filled with into the self-aligned emitter region, and a PN junction being formed between the emitter conductivity layer and the intrinsic base doped
25 region.

- Claim 2 (original): The bipolar junction transistor of claim 1 wherein the heavily doped polysilicon layer
30 is doped with a boron dopant with a dosage ranging from $1E19$ to $1E21$ atoms/cm³.

Claim 3 (original): The bipolar junction transistor of claim 1 wherein the substrate is a silicon substrate.

5 Claim 4 (original): The bipolar junction transistor of claim 1 wherein the substrate is a non-selective epitaxial silicon substrate.

10 Claim 5 (original): The bipolar junction transistor of claim 1 further comprising a self-aligned silicide (salicide) layer formed on the emitter conductivity layer.

15 Claim 6 (original): The bipolar junction transistor of claim 1 further comprising a selective implant collector (SIC) region formed in the substrate beneath the intrinsic base doped region.

20 Claim 7 (currently amended): The bipolar junction transistor of claim 1 further comprising an extended conductivity layer formed on the silicon nitride ~~dielectric~~ layer electrically connected to the heavily doped polysilicon layer.

Claim 8 (canceled)

25 Claim 9 (original): The bipolar junction transistor of claim 7 wherein the extended conductivity layer is composed of in-situ doped polysilicon.

30 Claim 10 (canceled)

Claim 11 (currently amended): A hetero-junction bipolar

junction transistor (HBT) comprising:

- a substrate;
a dielectric layer formed on a predetermined region
of the substrate;
5 an opening formed in the dielectric layer, and a
portion of the substrate being exposed;
a SiGe epitaxial layer formed on a sidewall and a
bottom of the opening, and extending outside the
opening and above the dielectric layer;
10 a spacer formed on the SiGe epitaxial layer to define
a self-aligned emitter region in the opening;
and
an emitter conductivity layer being filled with into
the self-aligned emitter region, and a PN
15 junction being formed between the emitter
conductivity layer and the SiGe epitaxial layer.

Claim 12 (original): The hetero-junction bipolar
junction transistor of claim 11 wherein the substrate
20 is a silicon substrate.

Claim 13 (original): The hetero-junction bipolar
junction transistor of claim 11 wherein the substrate
is a non-selective epitaxial silicon substrate.

25 Claim 14 (original): The hetero-junction bipolar
junction transistor of claim 11 further comprising a
self-aligned silicide (salicide) layer formed on the
emitter conductivity layer.

30 Claim 15 (original): The hetero-junction bipolar
junction transistor of claim 11 further comprising a

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selective implant collector (SIC) region formed in the substrate beneath the SiGe epitaxial layer.

Claim 16 (canceled)

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Claim 17 (canceled)